SEMICONDUCTOR PRODUCT

2 S C 2 0 5 0

C.B.C

TYPE	NPN Epitaxial Planar
MATERIAL	Silicon
APPLICATION	High Frequency Power Amplifier for 27MHz Band AM/SSB Transceiver
OUTLINE	See Fig 1
CONECTION	See Fig 1

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

VCBO (V)	VCER *1 (V)	VEBO (V)	IC *2 (A)	PC (W)	Tj (°C)	Tstg (°C)
70	70	4.0	8	25	150	-55 ~ +150

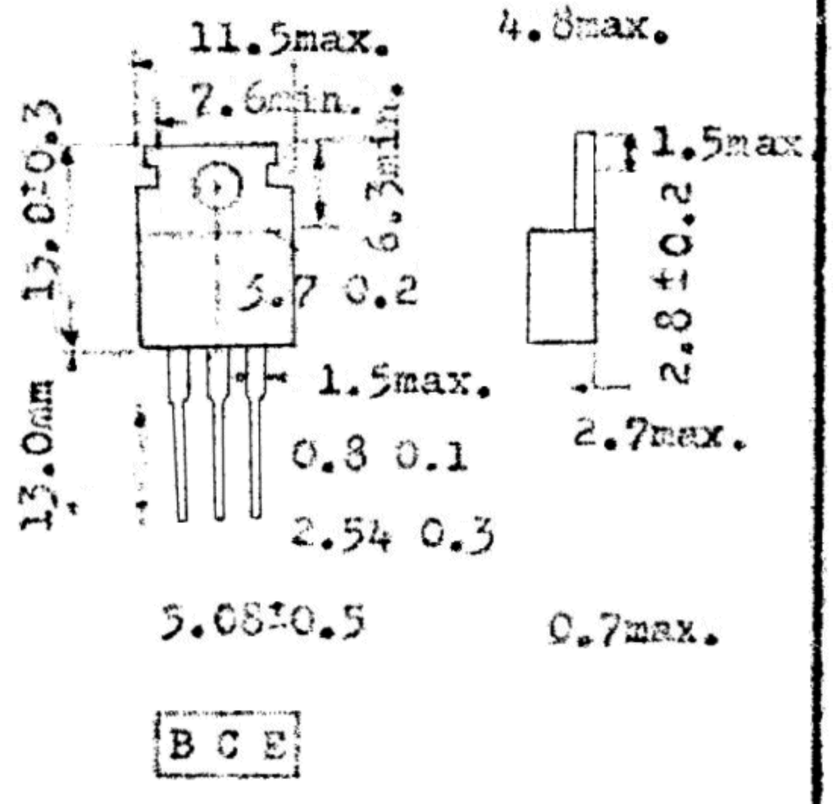
TEST SPECIFICATION Ta = 25°C

Symbol	Condition	Typ.	Limit		Unit
			Min	Max	
ICBO	VCB=40V, IE=0			20	μA
hFE	VCE=10V, IC=2.0A		20	150	
VCE(sat)	IC=2.0A, IB=0.4A	0.2		0.5	V
fT	VCE=10V, IC=0.5A	150			MHz
Cob	VCB=10V, f=1MHz, IE=0	80			PF
Po	VCC=12V, f=50MHz, Pi=3W		13.0		W
ηC	VCC=12V, f=50MHz, Pi=3W		60		%

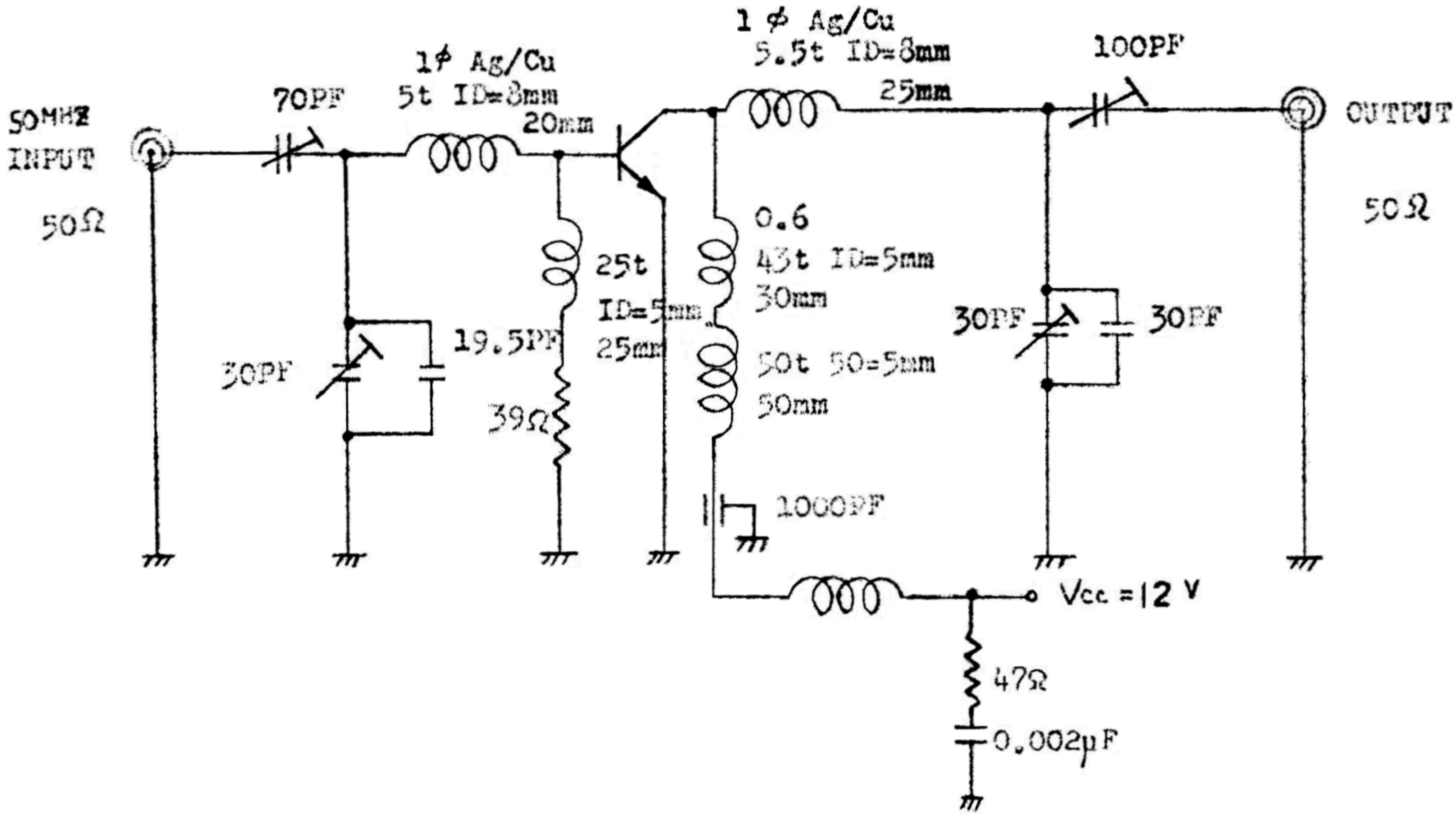
*1 RBE=100Ω

*2 PW=20mS, Duty Cycle 50%

Fig 1



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